

## ABSTRACT OF THE DISCLOSURE

A diode which eliminates the generation of local avalanche breakdown phenomenon when static surges in the backward direction are applied and has excellent properties to withstand 5 electrostatic breakdown is to be provided. A P-type impurity diffused region of high concentration to be an anode and an N-type impurity diffused region of high concentration to be a cathode that surrounds the P-type impurity diffused region are formed on the front surface of an N-type silicon well region. 10 The surface of the N-type silicon well region on which the impurity diffused regions are formed is covered with an interlayer dielectric, and a metal interconnect layer is formed thereon to spread to the border line of the N-type impurity diffused region and electrically connected to the P-type 15 impurity diffused region. Accordingly, a P-type inversion layer IP is uniformly formed in a separation area between the impurity diffused regions when static surges in the backward direction are applied, preventing a local avalanche breakdown phenomenon.